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Rohm Semiconductor RSS060P05FU6TB

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RSS060P05

# **Transistor**

# 4V Drive Pch MOS FET RSS060P05

#### Structure

Silicon P-channel MOS FET

#### ● Features

- 1) Built-in G-S Protection Diode.
- 2) Small and Surface Mount Package (SOP8).

# Applications

Power switching, DC / DC converter, Inverter

#### Packaging dimensions

	Package	Taping				
Type	Code	TB				
	Basic ordering unit (pieces)	2500				
RSS060P05		0				

# ● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage		$V_{DSS}$	-45	V
Gate-source voltage		$V_{GSS}$	±20	V
Drain current	Continuous	I <sub>D</sub>	±6.0	Α
	Pulsed	I <sub>DP</sub> *1	±24	Α
Source current	Continuous	I <sub>S</sub>	-1.6	Α
(Body diode)	Pulsed	I <sub>SP</sub> *1	-24	Α
Total power dissipation	P <sub>D *2</sub>	2	W	
Chanel temperature	$T_{ch}$	150	°C	
Range of Storage temperature		$T_{stg}$	-55 to +150	°C

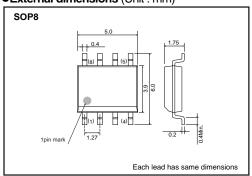
<sup>\*1</sup> PW≤10µs, Duty cycle≤1%\*2 Mounted on a ceramic board

#### ●Thermal resistance

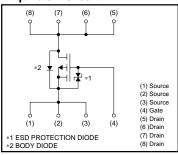
Parameter	Symbol	Limits	Unit
Chanel to ambient	R <sub>th(ch-a)</sub> *	62.5	°C/W

<sup>\*</sup> Mounted on a ceramic board

#### ●External dimensions (Unit : mm)



#### ●Equivalent circuit





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# ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I <sub>GSS</sub>	_	_	±10	μА	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR)</sub> DSS	-45	-	_	٧	I <sub>D</sub> = -1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	-	-	-1	μА	V <sub>DS</sub> = -45V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	-1.0	ı	-2.5	V	$V_{DS}$ = -10V, $I_{D}$ = -1mA
		ı	26	36	mΩ	I <sub>D</sub> = -6A, V <sub>G</sub> S= -10V
Static drain-source on-state resistance	R <sub>DS (on)</sub> *	ı	35	49	mΩ	I <sub>D</sub> = -6A, V <sub>G</sub> S= -4.5V
resistance		ı	38	53	mΩ	I <sub>D</sub> = -6A, V <sub>G</sub> S= -4.0V
Forward transfer admittance	Y <sub>fs</sub> *	8.0	ı	_	S	$V_{DS} = -10V, I_{D} = -6A$
Input capacitance	Ciss	ı	2700	_	pF	V <sub>DS</sub> = -10V
Output capacitance	Coss	ı	360	_	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	ı	230	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	ı	25	_	ns	Vpp≒ –25V
Rise time	tr *	ı	28	_	ns	ID= -3.0A   VGS= -10V
Turn-off delay time	t <sub>d (off)</sub> *	ı	100	_	ns	VGS= -10V   RL=-8.3Ω
Fall time	t <sub>f</sub> *	ı	28	_	ns	R <sub>G</sub> =10Ω
Total gate charge	Qg *	ı	23.0	32.2	nC	V <sub>DD</sub> ≒-25V V <sub>GS</sub> =-5V
Gate-source charge	Q <sub>gs</sub> *	ı	6.6	_	nC	I <sub>D</sub> = -6.0A
Gate-drain charge	Q <sub>gd</sub> *		8.0	_	nC	RL= $4.2\Omega$ R <sub>G</sub> = $10\Omega$

<sup>\*</sup>Pulsed

# ●Body diode characteristics (Source-Drain)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp*	_	-	-1.2	V	I <sub>S</sub> = -6A, V <sub>GS</sub> =0V

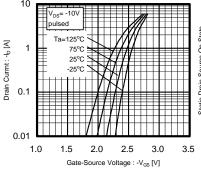
<sup>\*</sup>Pulsed

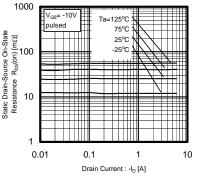


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#### Electrical characteristic curves





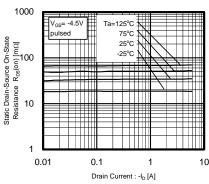
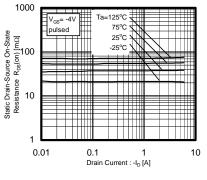
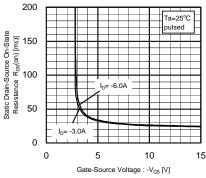


Fig.1 Typical Transfer Characteristics

Fig.2 Static Drain-Source On-State Resistance vs. Drain Current (1)

Fig.3 Static Drain-Source On-State Resistance vs. Drain Current (2)





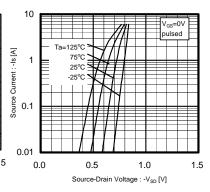
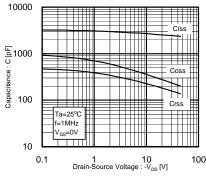
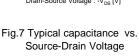


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (3)

Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

Fig.6 Source-Current vs. Source-Drain Voltage





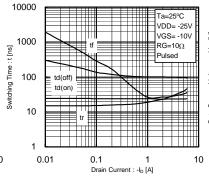


Fig.8 Switching Characteristics

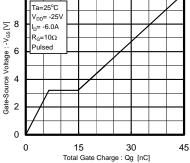


Fig.9 Dynamic Input Characteristics

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#### ●Measurement circuits

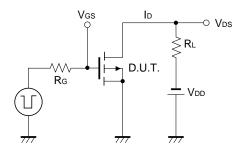


Fig.10 Switching Time Test Circuit

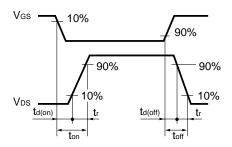


Fig.11 Switching Time Waveforms

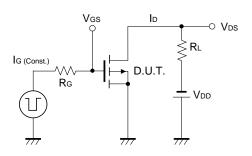


Fig.12 Gate Charge Test Circuit

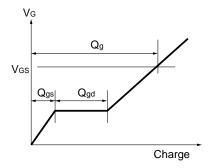


Fig.13 Gate Charge Waveform

# Distributor of Rohm Semiconductor: Excellent Integrated System Limited

Datasheet of RSS060P05FU6TB - MOSFET P-CH 45V 6A 8-SOIC

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# **Appendix**

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